# 2.5V Drive Pch MOS FET RTE002P02

#### ●Structure

Silicon P-channel MOS FET

## ● Features

- 1) Low On-resistance.
- 2) Small package (EMT3).
- 3) 2.5V drive.

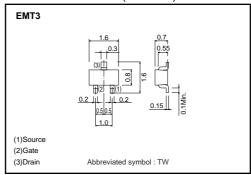
# Applications

Switching

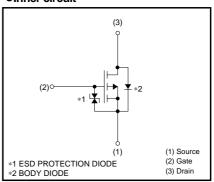
#### Package specifications

	Package	Taping
Type	Code	TL
	Basic ordering unit (pieces)	3000
RTE002P02		0

# ●External dimensions (Unit : mm)



#### •Inner circuit



# ● Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit			
Drain-source voltage		$V_{DSS}$	-20	V			
Gate-source voltage		V <sub>GSS</sub>	±12	V			
Drain augrant	Continuous	ID	±0.2	Α			
Drain current	Pulsed	I <sub>DP</sub> *1	±0.4	A			
Total power dissipation		P <sub>D</sub> *2	0.15	W			
Channel temperature		Tch	150	°C			
Range of storage temperature		Tstg	-55 to +150	°C			

<sup>\*1</sup> Pw≤10μs, Duty cycle≤1%

#### Thermal resistance

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a)*	833	°C/W

<sup>\*</sup> Each terminal mounted on a recommended land

<sup>\*2</sup> Each terminal mounted on a recommended land

# ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	_	_	±10	μА	Vgs= ±12V, Vps=0V
Drain-source breakdown voltage	V <sub>(BR) DSS</sub>	-20	_	_	V	I <sub>D</sub> = -1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	I <sub>DSS</sub>	_	_	-1	μΑ	V <sub>DS</sub> = -20V, V <sub>GS</sub> =0V
Gate threshold voltage	V <sub>GS (th)</sub>	-0.7	_	-2.0	V	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA
Static drain-source on-state resistance		_	1.0	1.5	Ω	I <sub>D</sub> = -0.2A, V <sub>G</sub> S= -4.5V
	R <sub>DS</sub> (on)*	_	1.1	1.6	Ω	I <sub>D</sub> = -0.2A, V <sub>G</sub> S= -4V
		_	2.0	3.0	Ω	I <sub>D</sub> = -0.15A, V <sub>G</sub> S= -2.5V
Forward transfer admittance	Y <sub>fs</sub> *	0.2	_	_	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.15A
Input capacitance	Ciss	_	50	_	pF	V <sub>DS</sub> = -10V
Output capacitance	Coss	_	5	_	pF	Vgs= 0V
Reverse transfer capacitance	Crss	_	5	_	pF	f=1MHz
Turn-on delay time	t <sub>d (on)</sub> *	_	9	_	ns	V <sub>DD</sub> ≒ −15V
Rise time	tr *	_	6	_	ns	I <sub>D</sub> = -0.15A   V <sub>G</sub> s= -4.5V
Turn-off delay time	t <sub>d (off)</sub> *	_	35	_	ns	$R_{L}=100\Omega$
Fall time	t <sub>f</sub> *	_	45	_	ns	R <sub>G</sub> = 10Ω

\*Pulsed

# ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsp	-	_	-1.2	V	I <sub>S</sub> = -0.1A, V <sub>GS</sub> =0V

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